TECHNICAL DATA DATA SHEET 5399, REV. -

HERMETIC RAD HARD POWER MOSFET

FEATURES:

- Low RDS(on)
- Single Event Effect (SEE) hardened, LET 55, Range: 90µm
 - VGS = -15V, VDS = 250V
 - VGS = -20V, VDS = 160V
- Total Ionization Dose (TID) hardened, 100kRad
- Surface mount SMD-2 package
- Near equivalent to IRHNA67260

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_c = 25$ °C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE VOLTAGE	V_{DS}	-	-	250	Volts
GATE TO SOURCE VOLTAGE	V_{GS}	ı	-	±20	Volts
ON-STATE DRAIN CURRENT	I_D	1	-	54	Amps
PULSED DRAIN CURRENT (LIMITED BY T _{JMAX})	I _{DM}	-	-	214	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P_{D}	1	-	250	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	0.5	°C/W
SINGLE PULSE AVALANCHE (LIMITED BY T _{JMAX})	E _{AS}	-	380	-	mJ

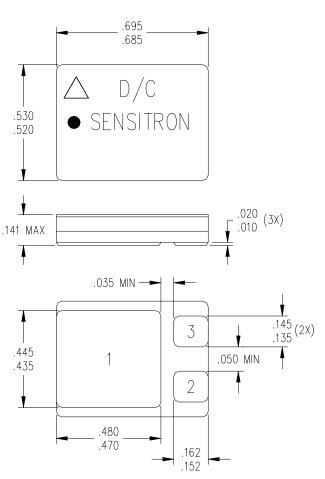
ELECTRICAL CHARACTERISTICS

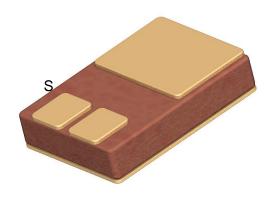
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE	B _{VDSS}	250	-	-	Volts
$V_{GS} = 0V, I_D = 250 \mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE	R _{DS(ON)}	-	-	0.03	Ω
$V_{GS} = 10V, I_D = 34A$					
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, $I_D = 1$ mA	$V_{GS(th)}$	2.0	-	4.0	Volts
ZERO GATE VOLTAGE DRAIN CURRENT					
$V_{DS} = 200V, V_{GS} = 0V$	I _{DSS}	-	-	25	μΑ
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20V$	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20V$		-	-	-100	
TRANSCONDUCTANCE $V_{DS} = 20V, I_{DS} = 34A$		-	22	-	S
TURN ON DELAY TIME $V_{DD} = 0.5V_{DS}$,	$t_{d(ON)}$	-	-	80	
RISE TIME $I_D = 34A$,	t _r	-	-	80	nsec
TURN OFF DELAY TIME $R_G = 4.7\Omega$	$t_{d(OFF)}$	-	-	130	
FALL TIME	t _f	-	-	80	
DIODE FORWARD VOLTAGE I _S = 54A	V_{SD}	-	-	1.2	Volts
REVERSE RECOVERY TIME	t _{rr}	-	-	700	nsec
$If = 50A$, $di/dt = 100A/\mu s$					
INPUT CAPACITANCE $V_{GS} = 0 \text{ V}$	C _{iss}	-	11100	-	
OUTPUT CAPACITANCE $V_{DS} = 100 \text{ V}$	Coss		696		pF
REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C _{rss}		11		·
GATE RESISTANCE	R_G	-	0.9	-	Ω
TOTAL GATE CHARGE	Q_{G}	-	-	180	nC
$V_{DD} = 0.5 V_{DS}, I_D = 54 A, V_{GS} = 10 V$					

^{**}NOTE: This product is subject to the International Traffic in Arms Regulations (ITAR), 22 C.F.R. Parts 120 - 130, and may not be exported without the appropriate U.S. Department of State authorization.

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MECHANICAL DIMENSIONS: in Inches / mm





<u>SMD-2</u>

DEVICE TYPE	PIN-1	PIN-2	PIN-3
N-CHANNEL MOSFET	DRAIN	GATE	SOURCE
SMD-2 PACKAGE			

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